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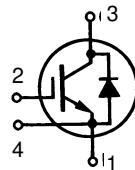
# High Voltage IGBT with Diode

Short Circuit SOA Capability

**IXSN 55N120AU1**

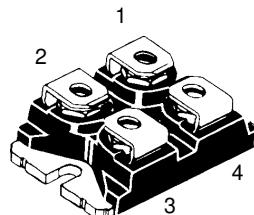
$V_{CES}$	=	1200 V
$I_{C25}$	=	110 A
$V_{CE(sat)}$	=	4 V

Preliminary data



Symbol	Test Conditions	Maximum Ratings		
$V_{CES}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	1200	V	
$V_{CGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ ; $R_{GE} = 1 \text{ M}\Omega$	1200	A	
$V_{GES}$	Continuous	$\pm 20$	V	
$V_{GEM}$	Transient	$\pm 30$	V	
$I_{C25}$	$T_c = 25^\circ\text{C}$	110	A	
$I_{C90}$	$T_c = 90^\circ\text{C}$	55	A	
$I_{CM}$	$T_c = 25^\circ\text{C}$ , 1 ms	160	A	
<b>SSOA (RBSOA)</b>	$V_{GE} = 15 \text{ V}$ , $T_{VJ} = 125^\circ\text{C}$ , $R_G = 22 \Omega$ Clamped inductive load, $L = 30 \mu\text{H}$	$I_{CM} = 110$ @ 0.8 $V_{CES}$	A	
<b><math>t_{sc}</math> (SCSOA)</b>	$V_{GE} = 15 \text{ V}$ , $V_{CE} = 0.6 \cdot V_{CES}$ , $T_J = 125^\circ\text{C}$ $R_G = 22 \Omega$ , non repetitive	10	$\mu\text{s}$	
<b><math>P_c</math></b>	$T_c = 25^\circ\text{C}$	IGBT	500	W
<b><math>P_d</math></b>		Diode	175	W
<b><math>V_{ISOL}</math></b>	50/60 Hz	$t = 1 \text{ min}$	2500	$\text{V}_\text{~}$
	$I_{ISOL} \leq 1 \text{ mA}$	$t = 1 \text{ s}$	3000	$\text{V}_\text{~}$
<b><math>T_J</math></b>		-55 ... +150	$^\circ\text{C}$	
<b><math>T_{JM}</math></b>		150	$^\circ\text{C}$	
<b><math>T_{stg}</math></b>		-55 ... +150	$^\circ\text{C}$	
<b><math>M_d</math></b>	Mounting torque	1.5/13	Nm/lb.in.	
	Terminal connection torque (M4)	1.5/13	Nm/lb.in.	

miniBLOC, SOT-227 B



## Features

- International standard package miniBLOC (ISOTOP) compatible
- Aluminium-nitride isolation
  - high power dissipation
- Isolation voltage 3000 V $\text{~}$
- Low  $V_{CE(sat)}$ 
  - for minimum on-state conduction losses
- Fast Recovery Epitaxial Diode
  - short  $t_{rr}$  and  $I_{RM}$
- Low collector-to-case capacitance (< 60 pF)
  - reduces RFI
- Low package inductance (< 10 nH)
  - easy to drive and to protect

Symbol	Test Conditions	Characteristic Values		
		( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$BV_{CES}$	$I_c = 8 \text{ mA}$ , $V_{GE} = 0 \text{ V}$	1200		V
$V_{GE(th)}$	$I_c = 8 \text{ mA}$ , $V_{CE} = V_{GE}$	4		V
$I_{CES}$	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0 \text{ V}$	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$	1 16	mA mA
$I_{GES}$	$V_{CE} = 0 \text{ V}$ , $V_{GE} = \pm 20 \text{ V}$		$\pm 200$	nA
$V_{CE(sat)}$	$I_c = I_{C90}$ , $V_{GE} = 15 \text{ V}$		4	V

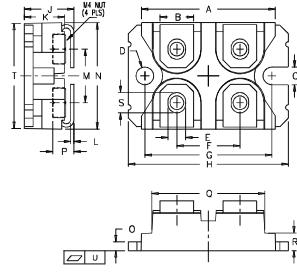
## Applications

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies

## Advantages

- Space savings
- Easy to mount with 2 screws
- High power density

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$g_{fs}$	$I_C = I_{C90}$ ; $V_{CE} = 10 \text{ V}$ , Pulse test, $t \leq 300 \mu\text{s}$ , duty cycle $d \leq 2\%$	32	45	S
$I_{C(on)}$	$V_{CE} = 10 \text{ V}$ , $V_{GE} = 15 \text{ V}$		340	A
$C_{ies}$	$V_{CE} = 25 \text{ V}$ , $V_{GE} = 0 \text{ V}$ , $f = 1 \text{ MHz}$	8000	pF	
$C_{oes}$		590	pF	
$C_{res}$		90	pF	
$Q_g$	$I_C = I_{C90}$ , $V_{GE} = 15 \text{ V}$ , $V_{CE} = 0.5 \cdot V_{CES}$	300	nC	
$Q_{ge}$		80	nC	
$Q_{gc}$		140	nC	
$t_{d(on)}$	<b>Inductive load, <math>T_J = 25^\circ\text{C}</math></b> $I_C = I_{C90}$ , $V_{GE} = 15 \text{ V}$ , $V_{CE} = 0.8 \cdot V_{CES}$ , $R_G = 2.7 \Omega$ Remarks: Switching times may increase for $V_{CE}$ (Clamp) > $0.8 \cdot V_{CES}$ , higher $T_J$ or increased $R_G$	140	ns	
$t_{ri}$		220	ns	
$t_{d(off)}$		400	ns	
$t_{fi}$		700	1000	ns
$E_{off}$		18	mJ	
$t_{d(on)}$	<b>Inductive load, <math>T_J = 125^\circ\text{C}</math></b> $I_C = I_{C90}$ , $V_{GE} = 15 \text{ V}$ , $V_{CE} = 0.8 \cdot V_{CES}$ , $R_G = 2.7 \Omega$ Remarks: Switching times may increase for $V_{CE}$ (Clamp) > $0.8 \cdot V_{CES}$ , higher $T_J$ or increased $R_G$	140	ns	
$t_{ri}$		250	ns	
$t_{d(off)}$		600	ns	
$t_{fi}$		900	ns	
$t_c$		950	ns	
$E_{on}$		6	mJ	
$E_{off}$		25	mJ	
$R_{thJC}$			0.25	K/W
$R_{thCK}$			0.05	K/W

**miniBLOC, SOT-227 B**

M4 screws (4x) supplied

Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	38.00	38.23	1.496	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.76	0.84	0.030	0.033
M	12.60	12.85	0.496	0.506
N	25.15	25.42	0.990	1.001
O	1.98	2.13	0.078	0.084
P	4.95	5.97	0.195	0.235
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.174
S	4.72	4.85	0.186	0.191
T	24.59	25.07	0.968	0.987
U	-0.05	0.1	-0.002	0.004

**Reverse Diode (FRED)****Characteristic Values**(T<sub>J</sub> = 25°C, unless otherwise specified)

Symbol	Test Conditions	min.	typ.	max.
$V_F$	$I_F = I_{C90}$ , $V_{GE} = 0 \text{ V}$ , Pulse test, $t \leq 300 \mu\text{s}$ , duty cycle $d \leq 2\%$		2.55	V
$I_{RM}$	$I_F = I_{C90}$ , $V_{GE} = 0 \text{ V}$ , $-di_F/dt = 480 \text{ A}/\mu\text{s}$ $V_R = 540 \text{ V}$ $I_F = 1 \text{ A}$ ; $-di/dt = 200 \text{ A}/\mu\text{s}$ ; $V_R = 30 \text{ V}$	32	36	A
$t_{rr}$		300	ns	
		40	60	ns
$T_J = 100^\circ\text{C}$				
$T_J = 25^\circ\text{C}$				
$R_{thJC}$			0.71	K/W